BUK7K17-60E

Dual N-channel 60 V, 14 m Ω standard level MOSFET

10 December 2013

Product data sheet

1. General description

Dual standard level N-channel MOSFET in an LFPAK56D (Dual Power-SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Dual MOSFET
- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with V_{GS(th)} of greater than 1 V at 175 °C

3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	60	V
I _D	drain current	V _{GS} = 10 V; Tmb = 25 °C; <u>Fig. 1</u>	[1]	-	-	30	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	53	W
Static characteristics FET1 and FET2							
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11		-	11.3	14	mΩ
Dynamic characteristics FET1 and FET2							
Q_{GD}	gate-drain charge	$I_D = 10 \text{ A}; V_{DS} = 48 \text{ V}; V_{GS} = 20 \text{ V};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 13}}; \underline{\text{Fig. 14}}$		-	8.1	-	nC

[1] Continuous current is limited by package



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Pinning information

Table 2. **Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1	8 7 6 5	D1 D1 D2 D2
2	G1	gate1	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	
3	S2	source2		
4	G2	gate2		
5	D2	drain2		
6	D2	drain2	1 2 3 4	mbk725
7	D1	drain1	1 2 3 4 LFPAK56D (SOT1205)	
8	D1	drain1		

Ordering information

Table 3. **Ordering information**

Type number	Package					
	Name	Description	Version			
BUK7K17-60E	LFPAK56D	Plastic single ended surface mounted package (LFPAK56D); 8 leads	SOT1205			

Marking

Table 4. **Marking codes**

Type number	Marking code
BUK7K17-60E	71760E

Limiting values 8.

Table 5. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	60	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 k Ω		-	60	V
V_{GS}	gate-source voltage	T _j ≤ 175 °C; DC		-20	20	V
I _D	drain current	V _{GS} = 10 V; Tmb = 25 °C; <u>Fig. 1</u>	[1]	-	30	Α
		T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 1</u>		-	29	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; Fig. 4		-	164	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	53	W
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Symbol	Parameter	Conditions		Min	Max	Unit
T _{stg}	storage temperature			-55	175	°C
T _j	junction temperature			-55	175	°C
Source-drain	diode FET1 and FET2		1			
Is	source current	T _{mb} = 25 °C	[1]	-	30	Α
I _{SM}	peak source current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C		-	164	Α
Avalanche R	uggedness FET1 and FET2					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$I_D = 30 \text{ A; } V_{sup} \le 60 \text{ V; } V_{GS} = 10 \text{ V;}$ $T_{j(init)} = 25 \text{ °C; } Fig. 3$	[2][3]	-	55	mJ

- Continuous current is limited by package
- [2] Refer to application note AN10273 for further information
- Single-pulse avalanche rating limited by maximum junction temperature of 175 °C [3]

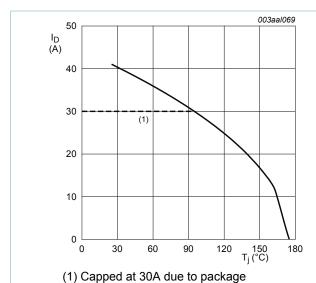
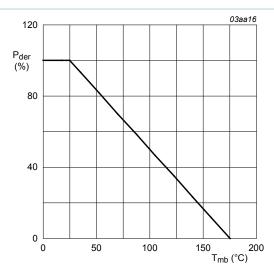


Fig. 1. Continuous drain current as a function of mounting base temperature

$$V_{GS} \ge 10V$$



Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

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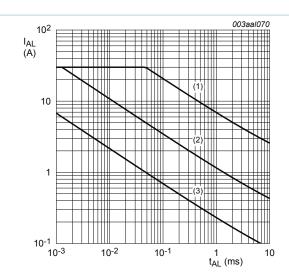
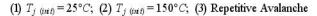


Fig. 3. Avalanche rating; avalanche current as a function of avalanche time



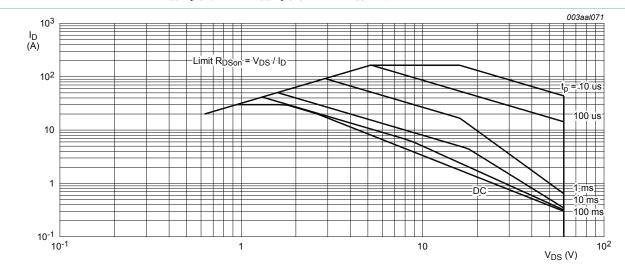


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb} = 25^{\circ}C; \ I_{DM}$ is a single pulse

9. Thermal characteristics

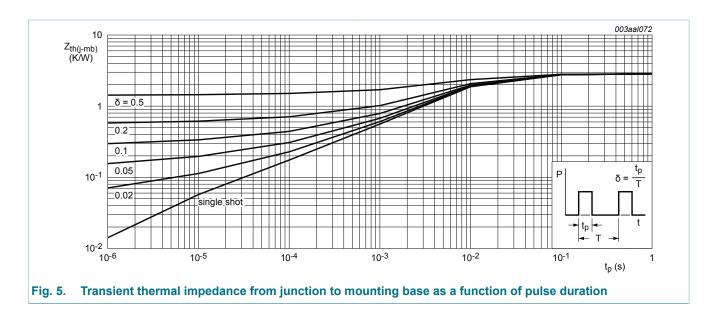
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	2.84	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	95	-	K/W

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10. Characteristics

Table 7. Characteristics

Parameter	Conditions	Min	Тур	Max	Unit
eristics FET1 and FET2					
drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	54	-	-	V
breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	60	-	-	V
gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10	2.4	3	4	V
	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 9; Fig. 10	1	-	-	V
	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; Fig. 9; Fig. 10	-	-	4.5	V
drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μA
	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μΑ
gate leakage current	V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
drain-source on-state resistance	V_{GS} = 10 V; I_D = 10 A; T_j = 25 °C; Fig. 11	-	11.3	14	mΩ
	V _{GS} = 10 V; I _D = 10 A; T _j = 175 °C; Fig. 11; Fig. 12	-	25.3	31.4	mΩ
cteristics FET1 and FE	T2		1		
total gate charge	I _D = 10 A; V _{DS} = 48 V; V _{GS} = 10 V;	-	23.6	-	nC
gate-source charge	T _i = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	_	4.9	_	nC
	gate-source threshold voltage drain leakage current gate leakage current drain-source on-state resistance	ristics FET1 and FET2 drain-source breakdown voltage $I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$ $I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ gate-source threshold voltage $I_D = 1 \ mA; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C;$ $Fig. 9; \ Fig. 10$ $I_D = 1 \ mA; \ V_{DS} = V_{GS}; \ T_j = 175 \ ^{\circ}C;$ $Fig. 9; \ Fig. 10$ $I_D = 1 \ mA; \ V_{DS} = V_{GS}; \ T_j = -55 \ ^{\circ}C;$ $Fig. 9; \ Fig. 10$ $I_D = 1 \ mA; \ V_{DS} = V_{GS}; \ T_j = -55 \ ^{\circ}C;$ $Fig. 9; \ Fig. 10$ $V_{DS} = 60 \ V; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ $V_{DS} = 60 \ V; \ V_{DS} = 0 \ V; \ T_j = 175 \ ^{\circ}C$ $V_{GS} = 20 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ $V_{GS} = 20 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C;$ $V_{GS} = 10 \ V; \ I_D = 10 \ A; \ T_j = 175 \ ^{\circ}C;$ $Fig. 11; \ Fig. 12$ $I_D = 10 \ A; \ V_{DS} = 48 \ V; \ V_{GS} = 10 \ V;$ $I_D = 10 \ A; \ V_{DS} = 10 \$	$ \begin{array}{l} \text{drain-source} \\ \text{breakdown voltage} \\ \text{I}_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}\text{C} \\ \text{I}_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}\text{C} \\ \text{I}_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}\text{C} \\ \text{I}_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}\text{C} \\ \text{I}_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}\text{C} \\ \text{I}_D = 1 \ \text{mA}; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}\text{C}; \\ \text{Fig. 9; Fig. 10} \\ \text{I}_D = 1 \ \text{mA}; \ V_{DS} = V_{GS}; \ T_j = 175 \ ^{\circ}\text{C}; \\ \text{Fig. 9; Fig. 10} \\ \text{I}_D = 1 \ \text{mA}; \ V_{DS} = V_{GS}; \ T_j = -55 \ ^{\circ}\text{C}; \\ \text{Fig. 9; Fig. 10} \\ \text{I}_D = 1 \ \text{mA}; \ V_{DS} = 0 \ \text{V}; \ T_j = 25 \ ^{\circ}\text{C} \\ \text{V}_{DS} = 60 \ \text{V}; \ V_{GS} = 0 \ \text{V}; \ T_j = 25 \ ^{\circ}\text{C} \\ \text{V}_{DS} = 60 \ \text{V}; 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\\ \hline \\ Fig. 9; \ Fig. 10 \\ \hline \\ I_D = 1 \ \text{mA}; \ V_{DS} = V_{GS}; \ T_j = 175 \ ^{\circ}\text{C}; \\ \hline \\ Fig. 9; \ Fig. 10 \\ \hline \\ I_D = 1 \ \text{mA}; \ V_{DS} = V_{GS}; \ T_j = -55 \ ^{\circ}\text{C}; \\ \hline \\ Fig. 9; \ Fig. 10 \\ \hline \\ I_D = 1 \ \text{mA}; \ V_{DS} = V_{GS}; \ T_j = -55 \ ^{\circ}\text{C}; \\ \hline \\ Fig. 9; \ Fig. 10 \\ \hline \\ I_D = 1 \ \text{mA}; \ V_{DS} = 0 \ \text{V}; \ T_j = 25 \ ^{\circ}\text{C} \\ \hline \\ V_{DS} = 60 \ \text{V}; \ V_{GS} = 0 \ \text{V}; \ T_j = 25 \ ^{\circ}\text{C} \\ \hline \\ V_{GS} = -20 \ \text{V}; \ V_{DS} = 0 \ \text{V}; \ T_j = 25 \ ^{\circ}\text{C} \\ \hline \\ V_{GS} = 20 \ \text{V}; \ V_{DS} = 0 \ \text{V}; \ T_j = 25 \ ^{\circ}\text{C} \\ \hline \\ V_{GS} = 20 \ \text{V}; \ V_{DS} = 0 \ \text{V}; \ T_j = 25 \ ^{\circ}\text{C}; \\ \hline \\ Fig. 11 \\ \hline \\ V_{GS} = 10 \ \text{V}; \ I_D = 10 \ \text{A}; \ T_j = 175 \ ^{\circ}\text{C}; \\ \hline \\ Fig. 11; \ Fig. 12 \\ \hline \\ \text{total gate charge} \\ \hline \\ \text{ID} = 10 \ \text{A}; \ V_{DS} = 48 \ \text{V}; \ V_{GS} = 10 \ \text{V}; \\ \hline \\ I_D = 10 \ \text{A}; \ V_{DS} = 10 \ \text{V}; \\ \hline \\ I_D = 10 \ \text{A}; \ V_{DS} = 10 \ \text{V}; \\ \hline \\ I_D = 10 \ \text{A}; \ V_{DS} = 10 \ \text{V}; \\ \hline \\ I_D = 10 \ \text{A}; \ V_{DS} = 10 \ \text{V}; \\ \hline \\ I_D = 10 \ \text{A}; \ V_{DS} = 10 \ \text{V}; \\ \hline \\ I_D = 10 \ \text{A}; \ V_{DS} = 10 \ \text{V}; \\ \hline \\ I_D = 10 \ \text{A}; \ V_{DS} = 10 \ \text{V}; \\ \hline \\ I_D = 10 \ \text{A}; \ V_{DS} = 10 \ \text{V}; \\ \hline \\ I_D = 10 \ \text{A}; \ V_{DS} = 10 \ \text{V}; \\ \hline \\ I_D = 10 \ \text{A}; \ V_{DS} = 10 \ \text{V}; \\ \hline \\ I_D = 10 \ \text{A}; \ V_{DS} = 10 \ \text{V}; \\ \hline \\ \hline \\ I_D = 10 \ \text{A}; \ V_{DS} = 10 \ \text{V}; \\ \hline \\ $	$ \begin{array}{l} \text{drain-source} \\ \text{breakdown voltage} \\ \text{FET1 and FET2} \\ \\ \text{I}_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}\text{C} \\ \\ \text{I}_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}\text{C} \\ \\ \text{I}_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}\text{C} \\ \\ \text{I}_D = 1 \ \text{mA}; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}\text{C}; \\ \\ \text{Fig. 9; Fig. 10} \\ \\ \text{I}_D = 1 \ \text{mA}; \ V_{DS} = V_{GS}; \ T_j = 175 \ ^{\circ}\text{C}; \\ \\ \text{Fig. 9; Fig. 10} \\ \\ \text{I}_D = 1 \ \text{mA}; \ V_{DS} = V_{GS}; \ T_j = -55 \ ^{\circ}\text{C}; \\ \\ \text{Fig. 9; Fig. 10} \\ \\ \text{I}_D = 1 \ \text{mA}; \ V_{DS} = V_{GS}; \ T_j = -55 \ ^{\circ}\text{C}; \\ \\ \text{Fig. 9; Fig. 10} \\ \\ \text{I}_D = 1 \ \text{mA}; \ V_{DS} = V_{GS}; \ T_j = -55 \ ^{\circ}\text{C}; \\ \\ \text{Fig. 9; Fig. 10} \\ \\ \text{I}_D = 1 \ \text{mA}; \ V_{DS} = 0 \ \text{V}; \ T_j = 25 \ ^{\circ}\text{C}; \\ \\ \text{Fig. 9; Fig. 10} \\ \\ \text{V}_{DS} = 60 \ \text{V}; \ V_{GS} = 0 \ \text{V}; \ T_j = 25 \ ^{\circ}\text{C}; \\ \\ \text{V}_{GS} = 20 \ \text{V}; \ V_{DS} = 0 \ \text{V}; \ T_j = 25 \ ^{\circ}\text{C}; \\ \\ \text{V}_{GS} = 20 \ \text{V}; \ V_{DS} = 0 \ \text{V}; \ T_j = 25 \ ^{\circ}\text{C}; \\ \\ \text{V}_{GS} = 20 \ \text{V}; \ V_{DS} = 0 \ \text{V}; \ T_j = 25 \ ^{\circ}\text{C}; \\ \\ \text{Fig. 11}; \\ \\ \text{V}_{GS} = 10 \ \text{V}; \ I_D = 10 \ \text{A}; \ T_j = 25 \ ^{\circ}\text{C}; \\ \\ \text{Fig. 11}; \ Fig. 12 \\ \\ \text{Intersitics FET1 and FET2} \\ \\ \text{total gate charge} \qquad \qquad \text{I}_D = 10 \ \text{A}; \ V_{DS} = 48 \ \text{V}; \ V_{GS} = 10 \ \text{V}; \\ \\ \text{I}_D = 10 \ \text{A}; \ V_{DS} = 10 \ \text{V}; \ T_D = 10 \ \text{A}; \ T_j = 175 \ ^{\circ}\text{C}; \\ \\ \text{Fig. 14}; \ \text{Fig. 14};$

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q_{GD}	gate-drain charge	$I_D = 10 \text{ A}; V_{DS} = 48 \text{ V}; V_{GS} = 20 \text{ V};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 13}}; \underline{\text{Fig. 14}}$	-	8.1	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 15}}$	-	1183	1578	pF
C _{oss}	output capacitance		-	167	200	pF
C _{rss}	reverse transfer capacitance		-	113	158	pF
t _{d(on)}	turn-on delay time	V_{DS} = 48 V; R_{L} = 5 Ω ; V_{GS} = 10 V; $R_{G(ext)}$ = 5 Ω ; T_{j} = 25 °C; I_{D} = 10 A	-	7.6	-	ns
t _r	rise time		-	11.1	-	ns
t _{d(off)}	turn-off delay time		-	15.5	-	ns
t _f	fall time		-	11	-	ns
Source-dra	ain diode FET1 and FET2					
V_{SD}	source-drain voltage	$I_S = 10 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}; Fig. 16$	-	0.78	1.2	V
t _{rr}	reverse recovery time	$I_S = 10 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	24.5	-	ns
Q _r	recovered charge	V _{DS} = 30 V; T _j = 25 °C	-	24.6	-	nC

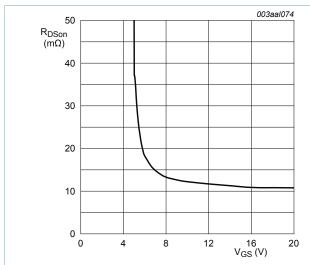
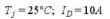


Fig. 6. Drain-source on-state resistance as a function of gate-source voltage; typical values



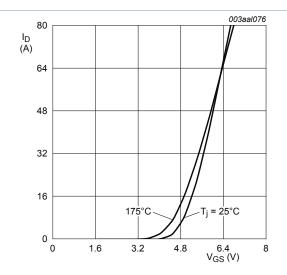


Fig. 7. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$$V_{DS} = 10V$$

10-1

10⁻²

10⁻³

 I_D (A)

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typ

max

003aah028

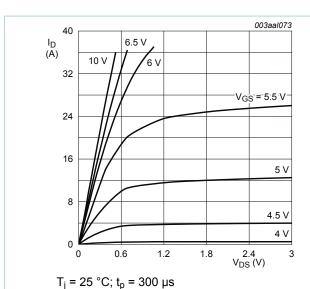
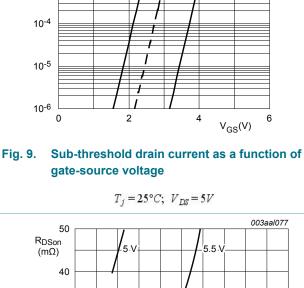


Fig. 8. Output characteristics; drain current as a function of drain-source voltage; typical values



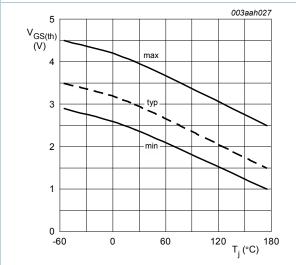
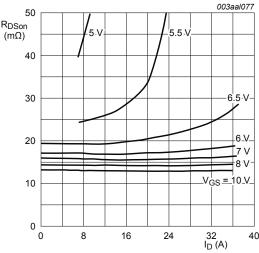


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}$$



 $T_i = 25 \, ^{\circ}C; t_p = 300 \, \mu s$

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

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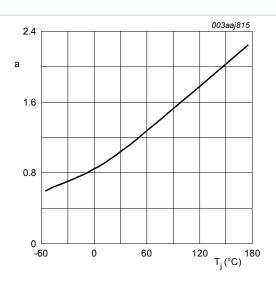


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon (25^{\circ}C)}}$$

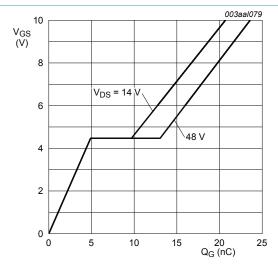


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25$$
°C; $I_D = 10A$

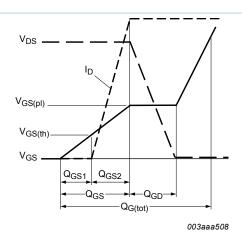


Fig. 13. Gate charge waveform definitions

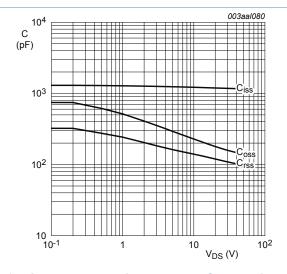


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = \mathbf{0}V; f = \mathbf{1}MHz$$

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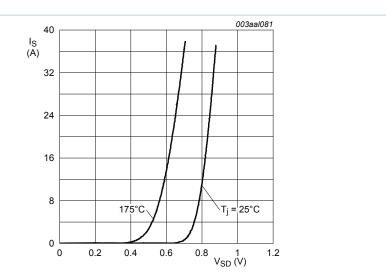


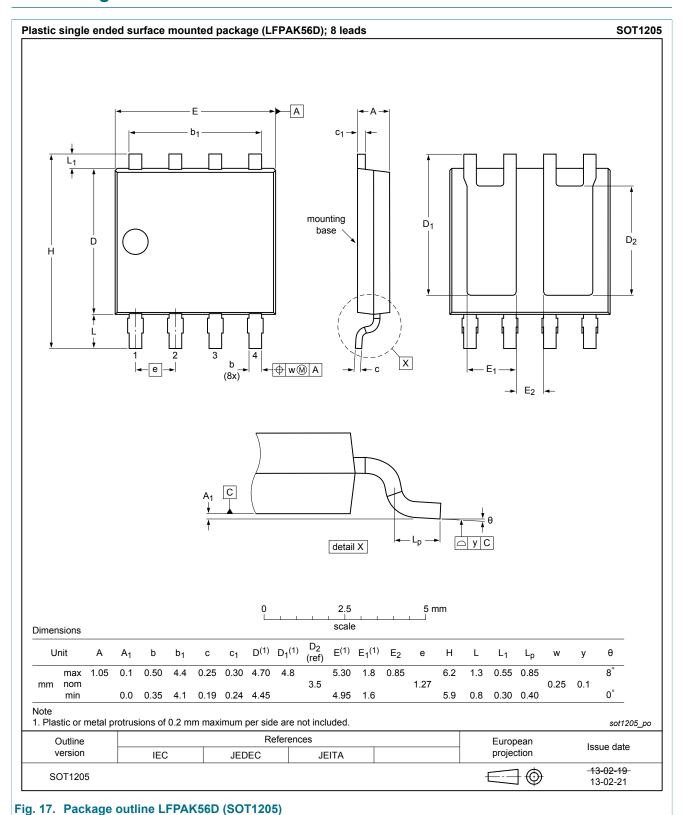
Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0V$$

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11. Package outline



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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Dual N-channel 60 V, 14 m Ω standard level MOSFET

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